

Thyristor Module

$$V_{RRM} = 1600 \text{ V}$$

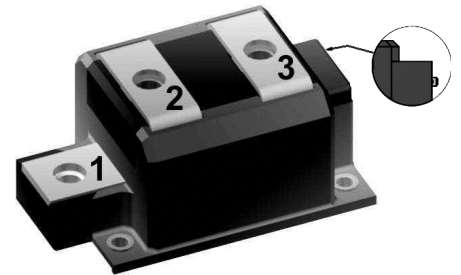
$$I_{TAV} = 1100 \text{ A}$$

$$V_T = 1.09 \text{ V}$$

Single Thyristor

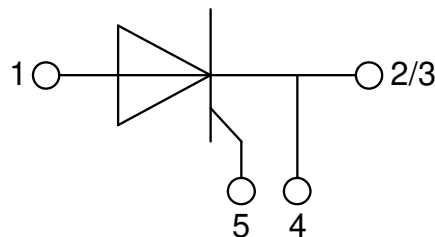
Part number

MCMA1400E1600CD



Backside: isolated

 E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al₂O₃-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: ComPack

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Base plate: Copper internally DCB isolated
- Advanced power cycling
- Phase Change Material available

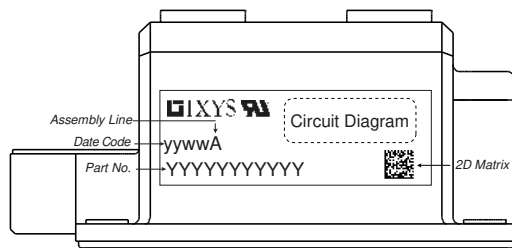
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Rectifier			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1700	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1600	V
I_{RD}	reverse current, drain current	$V_{R/D} = 1600 V$	$T_{VJ} = 25^{\circ}C$		4	mA
		$V_{R/D} = 1600 V$	$T_{VJ} = 125^{\circ}C$		80	mA
V_T	forward voltage drop	$I_T = 1000 A$	$T_{VJ} = 25^{\circ}C$		1.16	V
		$I_T = 2000 A$			1.43	V
		$I_T = 1000 A$	$T_{VJ} = 125^{\circ}C$		1.09	V
		$I_T = 2000 A$			1.42	V
I_{TAV}	average forward current	$T_C = 85^{\circ}C$	$T_{VJ} = 140^{\circ}C$		1100	A
$I_{T(RMS)}$	RMS forward current	180° sine			1700	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 140^{\circ}C$		0.80	V
r_T	slope resistance				0.29	mΩ
R_{thJC}	thermal resistance junction to case				0.03	K/W
R_{thCH}	thermal resistance case to heatsink			0.015		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		3800	W
I_{TSM}	max. forward surge current	$t = 10 ms; (50 Hz), sine$	$T_{VJ} = 45^{\circ}C$		36.0	kA
		$t = 8,3 ms; (60 Hz), sine$	$V_R = 0 V$		38.9	kA
		$t = 10 ms; (50 Hz), sine$	$T_{VJ} = 140^{\circ}C$		30.6	kA
		$t = 8,3 ms; (60 Hz), sine$	$V_R = 0 V$		33.1	kA
I^2t	value for fusing	$t = 10 ms; (50 Hz), sine$	$T_{VJ} = 45^{\circ}C$		6.48	MA ² s
		$t = 8,3 ms; (60 Hz), sine$	$V_R = 0 V$		6.29	MA ² s
		$t = 10 ms; (50 Hz), sine$	$T_{VJ} = 140^{\circ}C$		4.68	MA ² s
		$t = 8,3 ms; (60 Hz), sine$	$V_R = 0 V$		4.54	MA ² s
C_J	junction capacitance	$V_R = 400 V f = 1 MHz$	$T_{VJ} = 25^{\circ}C$	1.75		nF
P_{GM}	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 140^{\circ}C$		480	W
		$t_p = 300 \mu s$			240	W
P_{GAV}	average gate power dissipation				80	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 140^{\circ}C; f = 50 Hz$ repetitive, $I_T = 3000 A$			100	A/μs
		$t_p = 200 \mu s; di_G/dt = 1 A/\mu s;$ $I_G = 1 A; V = 2/3 V_{DRM}$ non-repet., $I_T = 1000 A$			500	A/μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = 2/3 V_{DRM}$	$T_{VJ} = 140^{\circ}C$		1000	V/μs
		$R_{GK} = \infty$; method 1 (linear voltage rise)				
V_{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		2	V
			$T_{VJ} = -40^{\circ}C$		3	V
I_{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		600	mA
			$T_{VJ} = -40^{\circ}C$		800	mA
V_{GD}	gate non-trigger voltage	$V_D = 2/3 V_{DRM}$	$T_{VJ} = 140^{\circ}C$		0.25	V
I_{GD}	gate non-trigger current				10	mA
I_L	latching current	$t_p = 30 \mu s$	$T_{VJ} = 25^{\circ}C$		800	mA
		$I_G = 1 A; di_G/dt = 1 A/\mu s$				
I_H	holding current	$V_D = 6 V R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		600	mA
t_{gd}	gate controlled delay time	$V_D = 1/2 V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	μs
		$I_G = 1 A; di_G/dt = 1 A/\mu s$				
t_q	turn-off time	$V_R = 100 V; I_T = -0.3 A; V = 2/3 V_{DRM}$ $di/dt = 10 A/\mu s dv/dt = 50 V/\mu s t_p = 200 \mu s$	$T_{VJ} = 125^{\circ}C$	350		μs

Package ComPack		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			1200	A
T_{VJ}	virtual junction temperature		-40		140	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				500		g
M_D	mounting torque		3		5	Nm
M_T	terminal torque		12		14	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	21.0			mm
$d_{Spb/Apb}$		terminal to backside	18.0			mm
V_{ISOL}	isolation voltage	t = 1 second	4800			V
		t = 1 minute	4000			V

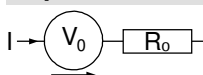

Part description

- M = Module
- C = Thyristor (SCR)
- M = Thyristor
- A = (up to 1800V)
- 1400 = Current Rating [A]
- E = Single Thyristor
- 1600 = Reverse Voltage [V]
- CD = ComPack

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCMA1400E1600CD	MCMA1400E1600CD	Box	3	521522

Equivalent Circuits for Simulation

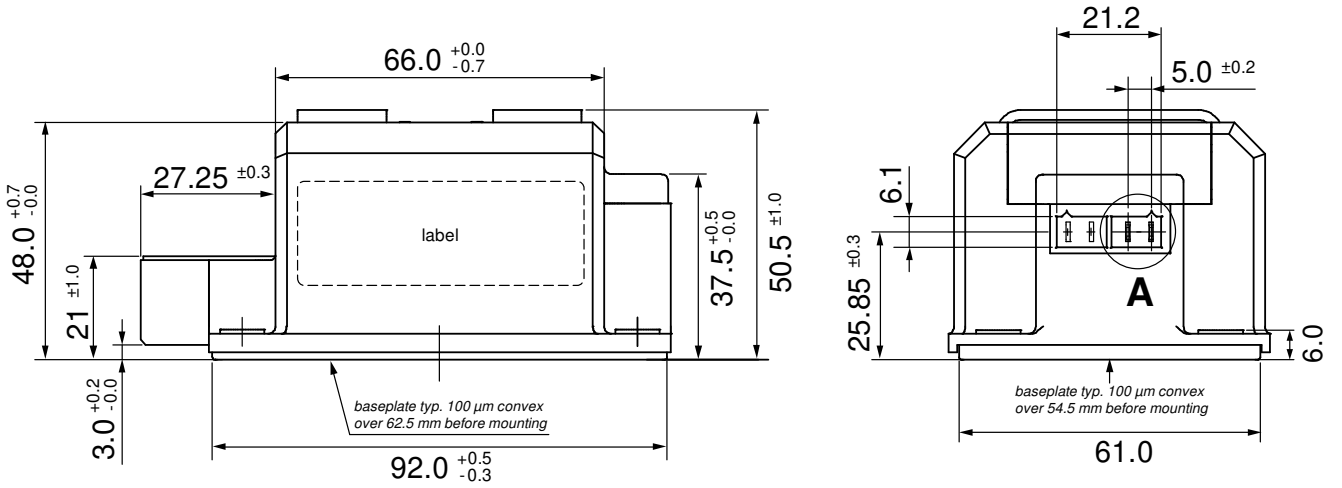
* on die level

 $T_{VJ} = 140^{\circ}\text{C}$

Thyristor

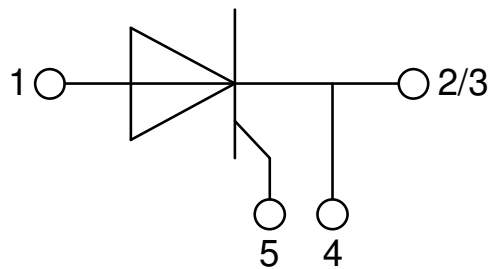
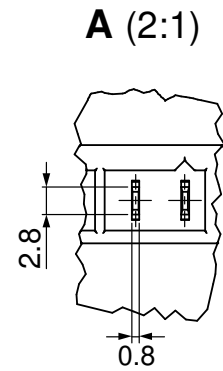
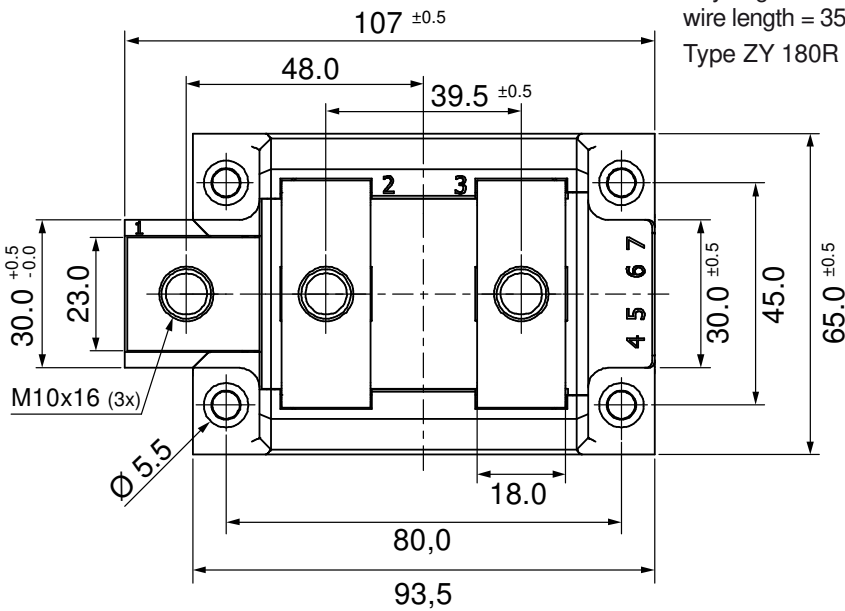
$V_{0\ max}$	threshold voltage	0.8	V
$R_{0\ max}$	slope resistance *	0.21	mΩ



Outlines ComPack



Optional accessories for modules
Keyed gate/cathode twin plug with
wire length = 350 mm, gate = white, cathode = red
Type ZY 180R (R = Right for pin pair 6/7) UL 758, style 3751



Thyristor

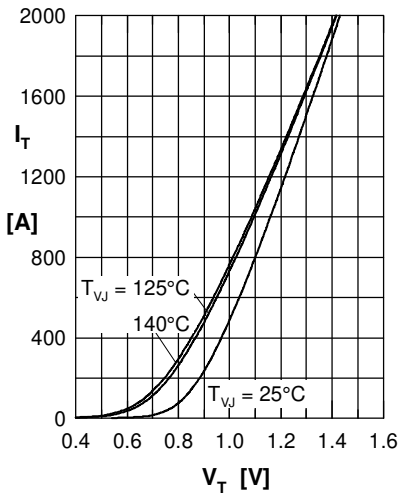


Fig. 1 Forward characteristics

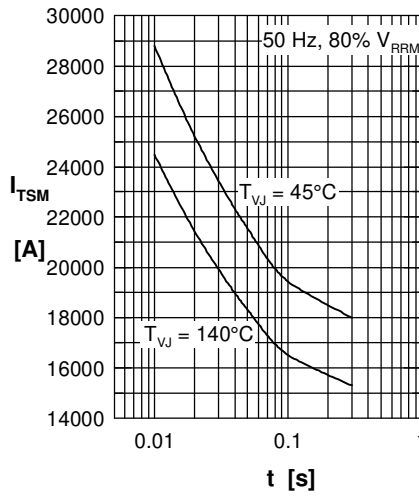


Fig. 2 Surge overload current
 I_{TSM} : crest value, t : duration

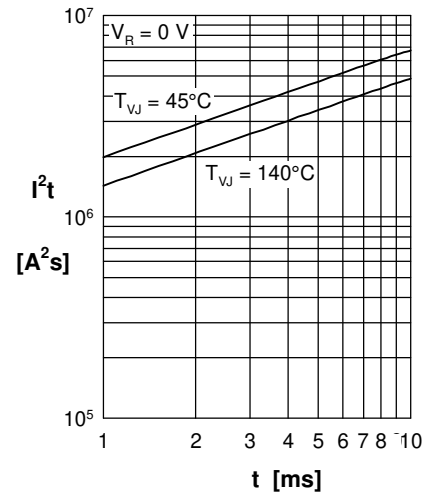


Fig. 3 I^2t versus time (1-10 s)

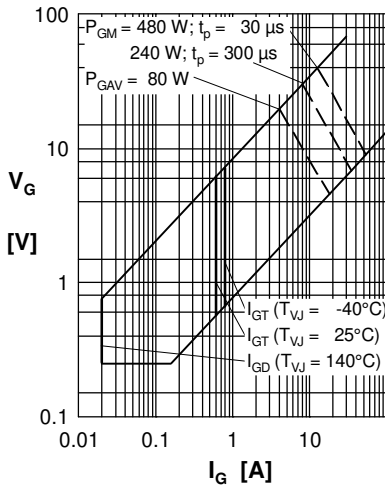


Fig. 4 Gate voltage & gate current

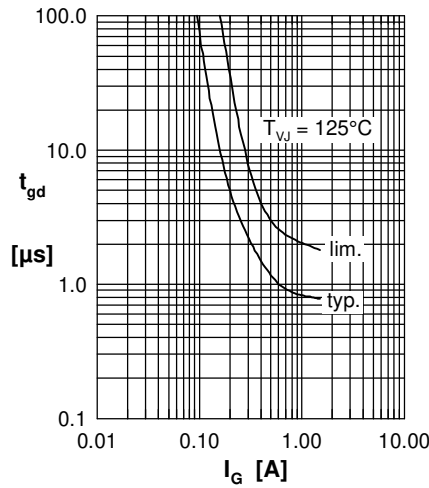


Fig. 5 Gate controlled delay time t_{gd}

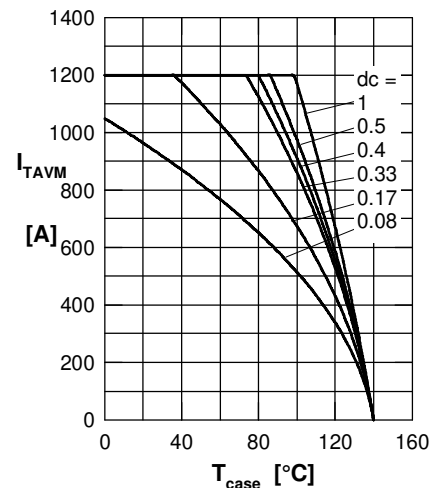


Fig. 6 Max. forward current at case temperature

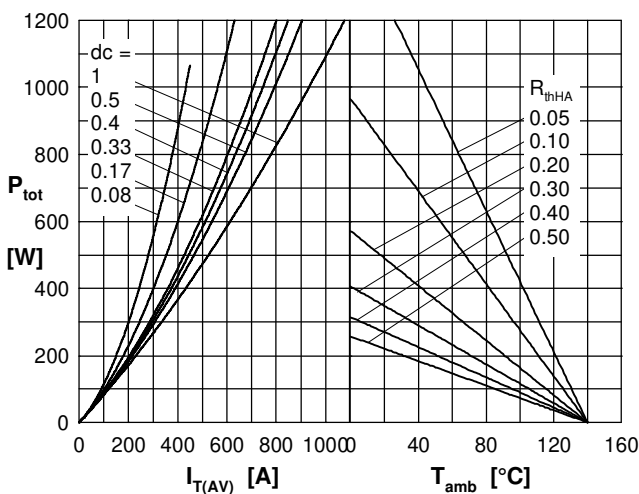


Fig. 7a Power dissipation versus direct output current
 Fig. 7b and ambient temperature

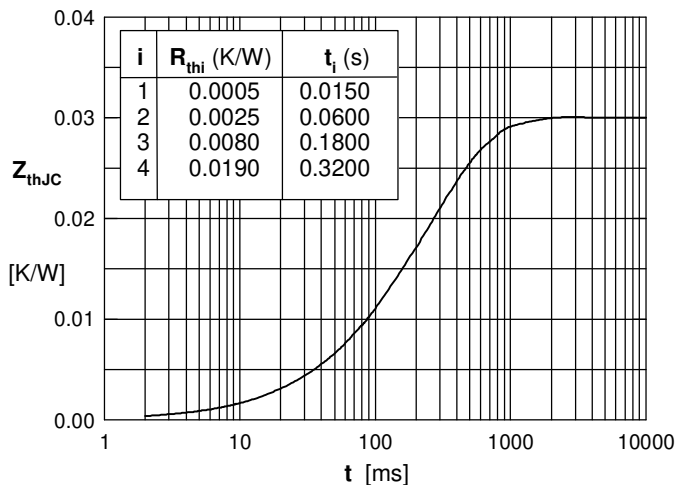


Fig. 8 Transient thermal impedance junction to case